

YAO-3950

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

O I P E S C I T
JAN 09 2002
PATENT & TRADEMARK OFFICE
Applicant: Yoshihisa Nagano et al.
Serial No.: 09/103,873
Filed: June 24, 1998

: Art Unit: 2815
: Examiner: J. Diaz
: RESPONSE UNDER
1.116
: EXPEDITED
PROCEDURE

For: SEMICONDUCTOR DEVICE AND
METHOD FOR FABRICATING THE SAME.

PRELIMINARY AMENDMENT AND REQUEST FOR
EXTENSION OF TIME

Assistant Commissioner for Patents
Washington, DC 20231

SIR:

Prior to examination, please amend the above-identified application
as follows:

IN THE DRAWINGS:

Please amend Figure 7 as indicated in red on the enclosed copy of
Figure 7.

CLAIMS:

Please cancel claim 28.

Please add claims 29-31:

1 29. (Newly Added) The semiconductor device of claim 1 wherein
2 the second interlayer insulating film provides substantially flat step coverage of the
3 first interconnect and the first interlayer insulating film.

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30. (Newly Added) The semiconductor device of claim 1 wherein
the dielectric film includes a remnant polarization of approximately $10 \mu\text{C}/\text{cm}^2$.

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T. Flowers
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